# Switching Diode, High Voltage, High Temperature

### **BASH19L Series**

#### **Features**

- 175°C T<sub>J(MAX)</sub> Rated for High Temperature, Mission Critical Applications
- NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

| Rating  | Symbol                            | Value             | Unit |
|---|-----------------------------------|-------------------|------|
| Continuous Reverse Voltage  BASH19  BASH20  BASH21  | V <sub>R</sub>                    | 120<br>200<br>250 | Vdc  |
| Repetitive Peak Reverse Voltage<br>BASH19<br>BASH20<br>BASH21                                     | V <sub>RRM</sub>                  | 120<br>200<br>250 | Vdc  |
| Continuous Forward Current  | lF                                | 200               | mAdc |
| Peak Forward Surge Current<br>(1/2 Cycle, Sine Wave, 60 Hz)                                       | I <sub>FSM</sub>                  | 2                 | А    |
| Repetitive Peak Forward Current<br>(Pulse Train: T <sub>ON</sub> = 1 s, T <sub>OFF</sub> = 0.5 s) | I <sub>FRM</sub>                  | 0.6               | Α    |
| Junction and Storage Temperature Range  | T <sub>J</sub> , T <sub>stg</sub> | -55 to +175       | °C   |
| Electrostatic Discharge   | ESD                               | HM < 500          | V    |
|   |                                   | MM < 400          | V    |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



#### ON Semiconductor®

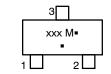
www.onsemi.com

## HIGH VOLTAGE SWITCHING DIODE



#### **MARKING DIAGRAM**





SOT-23 (TO-236) CASE 318 STYLE 8

AD7 = BASH19L
AC7 = BASH20L
AA7 = BASH21L
M = Date Code
• = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

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#### THERMAL CHARACTERISTICS

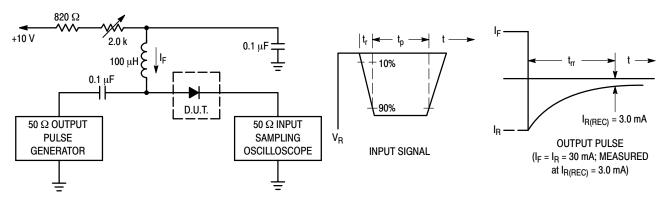
| Characteristic   | Symbol                            | Max         | Unit        |
|--|-----------------------------------|-------------|-------------|
| Total Device Dissipation FR-5 Board (Note 1) T <sub>A</sub> = 25°C         | P <sub>D</sub>                    | 300         | mW<br>mW/°C |
| Derate above 25°C  |                                   | 1.0         | IIIVV/ G    |
| Thermal Resistance Junction-to-Ambient (SOT-23)                            | $R_{\theta JA}$                   | 340         | °C/W        |
| Total Device Dissipation Alumina Substrate (Note 2)  T <sub>A</sub> = 25°C | P <sub>D</sub>                    | 400         | mW          |
| Derate above 25°C  |                                   | 2.4         | mW/°C       |
| Thermal Resistance Junction-to-Ambient                                     | $R_{\theta JA}$                   | 250         | °C/W        |
| Junction and Storage Temperature Range                                     | T <sub>J</sub> , T <sub>stg</sub> | -55 to +175 | °C          |

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.

#### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25$ °C unless otherwise noted)

| Characteristic  | Symbol | Min               | Max | Unit |      |
|---|--------|-------------------|-----|------|------|
| Reverse Voltage Leakage Current   |        | I <sub>R</sub>    |     |      | μAdc |
| (V <sub>R</sub> = 100 Vdc)  | BASH19 |                   | -   | 0.1  |      |
| (V <sub>R</sub> = 150 Vdc)  | BASH20 |                   | -   | 0.1  |      |
| (V <sub>R</sub> = 200 Vdc)  | BASH21 |                   | _   | 0.1  |      |
| $(V_R = 100 \text{ Vdc}, T_J = 175^{\circ}\text{C})$  | BASH19 |                   | _   | 100  |      |
| (V <sub>R</sub> = 150 Vdc, T <sub>J</sub> = 175°C)  | BASH20 |                   | _   | 100  |      |
| (V <sub>R</sub> = 200 Vdc, T <sub>J</sub> = 175°C)  | BASH21 |                   | -   | 100  |      |
| Reverse Breakdown Voltage   |        | V <sub>(BR)</sub> |     |      | Vdc  |
| (I <sub>BR</sub> = 100 μAdc)  | BASH19 | , ,               | 120 | _    |      |
| (I <sub>BR</sub> = 100 μAdc)  | BASH20 |                   | 200 | _    |      |
| (I <sub>BR</sub> = 100 μAdc)  | BASH21 |                   | 250 | -    |      |
| Forward Voltage   |        | V <sub>F</sub>    |     |      | Vdc  |
| (I <sub>F</sub> = 100 mAdc)   |        |                   | _   | 1.0  |      |
| (I <sub>F</sub> = 200 mAdc)   |        |                   | -   | 1.25 |      |
| Diode Capacitance (V <sub>R</sub> = 0, f = 1.0 MHz)   |        | C <sub>D</sub>    | -   | 5.0  | pF   |
| Reverse Recovery Time ( $I_F = I_R = 30 \text{ mAdc}$ , $I_{R(REC)} = 3.0 \text{ mAdc}$ , $R_L = 100$ ) |        | t <sub>rr</sub>   | -   | 50   | ns   |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



Notes: 1. A 2.0  $k\Omega$  variable resistor adjusted for a Forward Current (I<sub>F</sub>) of 30 mA.

- 2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 30 mA.
- 3.  $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

#### **TYPICAL CHARACTERISTICS**

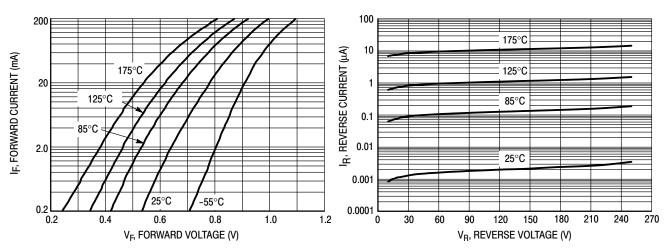


Figure 2. Forward Voltage

Figure 3. Leakage Current

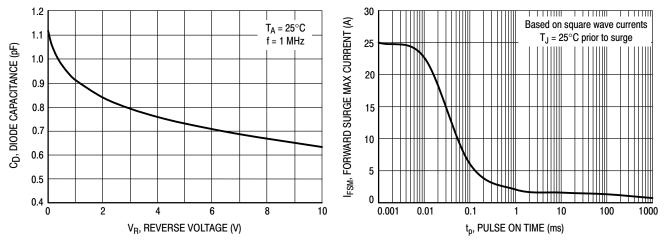


Figure 4. Capacitance

Figure 5. Forward Surge Current

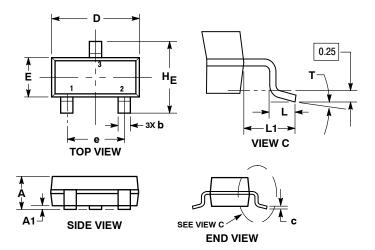
#### **ORDERING INFORMATION**

| Device         | Package             | Shipping <sup>†</sup> |
|----------------|---------------------|-----------------------|
| BASH19LT1G     | SOT-23<br>(Pb-Free) | 3000 / Tape & Reel    |
| NSVBASH19LT1G* | SOT-23<br>(Pb-Free) | 3000 / Tape & Reel    |
| BASH20LT1G     | SOT-23<br>(Pb-Free) | 3000 / Tape & Reel    |
| NSVBASH20LT1G* | SOT-23<br>(Pb-Free) | 3000 / Tape & Reel    |
| BASH21LT1G     | SOT-23<br>(Pb-Free) | 3000 / Tape & Reel    |
| NSVBASH21LT1G* | SOT-23<br>(Pb-Free) | 3000 / Tape & Reel    |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable – release available upon request.

#### PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AS** 



- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

|     | MILLIMETERS |      |      | INCHES |       |       |
|-----|-------------|------|------|--------|-------|-------|
| DIM | MIN         | NOM  | MAX  | MIN    | NOM   | MAX   |
| Α   | 0.89        | 1.00 | 1.11 | 0.035  | 0.039 | 0.044 |
| A1  | 0.01        | 0.06 | 0.10 | 0.000  | 0.002 | 0.004 |
| b   | 0.37        | 0.44 | 0.50 | 0.015  | 0.017 | 0.020 |
| С   | 0.08        | 0.14 | 0.20 | 0.003  | 0.006 | 0.008 |
| D   | 2.80        | 2.90 | 3.04 | 0.110  | 0.114 | 0.120 |
| E   | 1.20        | 1.30 | 1.40 | 0.047  | 0.051 | 0.055 |
| е   | 1.78        | 1.90 | 2.04 | 0.070  | 0.075 | 0.080 |
| L   | 0.30        | 0.43 | 0.55 | 0.012  | 0.017 | 0.022 |
| L1  | 0.35        | 0.54 | 0.69 | 0.014  | 0.021 | 0.027 |
| HE  | 2.10        | 2.40 | 2.64 | 0.083  | 0.094 | 0.104 |
| Т   | 0°          |      | 10°  | 0°     |       | 10°   |

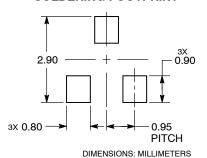
#### STYLE 8:

ANODE PIN 1.

NO CONNECTION

3 CATHODE

#### **RECOMMENDED SOLDERING FOOTPRINT**



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